

**IN THE CLAIMS:**

Please cancel claim 5, as shown in the complete list of claims that is presented below.

1. (previously presented) An ONO flash memory array for reducing disturbance between adjacent memory cells, comprising:

a substrate having first and second buried diffusion regions;

a channel between the first and second buried diffusion regions;

an ONO layer above the channel for memory storage;

a first pocket of a first concentration implanted on one side of the channel close to the first buried diffusion region; and

a second pocket of a second concentration implanted on the other side of the channel close to the second buried diffusion region, wherein the first concentration is higher than the second concentration.

Claim 2 (cancelled).

3. (previously presented) An ONO flash memory array for reducing disturbance between first and second adjacent memory cells, comprising:

a substrate having first and second buried diffusion regions, the second buried diffusion region having a first portion in the first memory cell and a second portion in the second memory cell;

a channel in the first memory between the first buried diffusion region and the first portion of the second buried diffusion region;

an ONO layer above the channel for memory storage in the first memory cell;

a first implanted pocket at the first portion of the second buried diffusion region, the first pocket having a first concentration; and

a second implanted pocket at the second portion of the second diffusion region, the second pocket having a second concentration that is different from the first concentration.

Claims 4 and 5 (cancelled).

6. (previously presented) An ONO flash memory array for reducing disturbance between first and second adjacent memory cells, comprising:

a substrate having first source/drain and second source/drain regions, the second source/drain region having a first portion in the first memory cell and a second portion in the second memory cell;

a channel in the first memory cell between the first source/drain region and the first portion of the second source/drain region;

an ONO layer above the channel for memory storage in the first memory cell; and

an implanted pocket arrangement nearby the second source/drain region that is asymmetrical with respect to the first and second portions thereof,

wherein the implanted pocket arrangement comprises a first implanted pocket at the first portion of the second source/drain region and a second implanted pocket at the second portion, the first and second implanted pockets having different concentrations.